

Is Now Part of



ON Semiconductor®

To learn more about ON Semiconductor, please visit our website at <u>www.onsemi.com</u>

Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (_), the underscore (_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.onsemi.com. Please email any questions regarding the system integration to Fairchild_questions@onsemi.com.

ON Semiconductor and the ON Semiconductor logo are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or unavteries, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out or i, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor and is officers, employees, uniotificated use, even if such claim any manner.





Data Sheet

September 2013

N-Channel Power MOSFET 60*V*, 50*A*, 22 mΩ

These N-Channel power MOSFETs are manufactured using the MegaFET process. This process, which uses feature sizes approaching those of LSI integrated circuits gives optimum utilization of silicon, resulting in outstanding performance. They were designed for use in applications such as switching regulators, switching converters, motor drivers, and relay drivers. These transistors can be operated directly from integrated circuits.

Formerly developmental type TA49018.

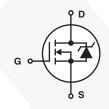
Ordering Information

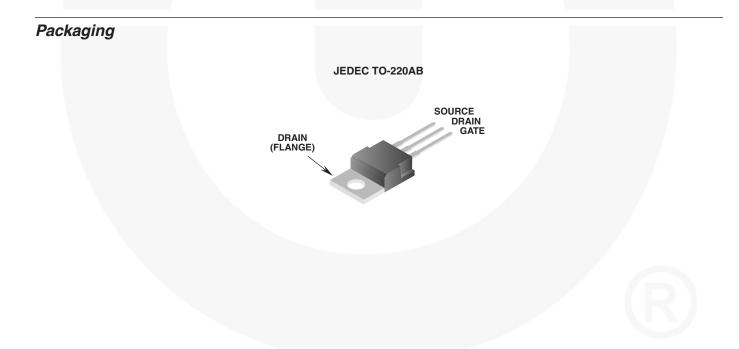
PART NUMBER	PACKAGE	BRAND	
RFP50N06	TO-220AB	RFP50N06	

Features

- 50A, 60V
- r_{DS(ON)} = 0.022Ω
- Temperature Compensating PSPICE[®] Model
- Peak Current vs Pulse Width Curve
- UIS Rating Curve
- 175⁰C Operating Temperature

Symbol





Absolute Maximum Ratings $T_C = 25^{\circ}C$, Unless Otherwise Specified

	RFP50N06	UNITS
Drain to Source Voltage (Note 1)V _{DSS}	60	V
Drain to Gate Voltage (R_{GS} = 20k Ω) (Note 1) V _{DGR}	60	V
Gate to Source VoltageV _{GS}	±20	V
Continuous Drain Current (Figure 2)	50 (Figure 5)	А
Pulsed Avalanche RatingE _{AS}	(Figure 6)	
Power Dissipation	131 0.877	W W/ ^o C
Operating and Storage Temperature	-55 to 175	°C
Maximum Temperature for Soldering Leads at 0.063in (1.6mm) from Case for 10sT _L Package Body for 10s, see Techbrief 334T _{pkg}	300 260	°C C°

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTE:

1. $T_J = 25^{\circ}C$ to $150^{\circ}C$.

Electrical Specifications $T_C = 25^{\circ}C$, Unless Otherwise Specified

PARAMETER	SYMBOL	TEST CONDITIONS		MIN	TYP	MAX	UNITS
Drain to Source Breakdown Voltage	BV _{DSS}	$I_{D} = 250 \mu A, V_{GS} = 0V$ (Figure 11)		60	-	-	V
Gate to Source Threshold Voltage	V _{GS(TH)}	$V_{GS} = V_{DS}$, $I_D = 250\mu A$ (Figure 10)		2	-	4	V
Zero Gate Voltage Drain Current	IDSS	$V_{DS} = 60V,$ $V_{GS} = 0V$	$T_{\rm C} = 25^{\rm o}{\rm C}$	-	-	1	μA
			$T_{\rm C} = 150^{\rm O}{\rm C}$	-	-	50	μA
Gate to Source Leakage Current	I _{GSS}	$V_{GS} = \pm 20V$		-	-	±100	nA
Drain to Source On Resistance	rDS(ON)	$I_{D} = 50A, V_{GS} = 1$	I0V (Figures 9)	-	-	0.022	Ω
Turn-On Time	ton	$V_{DD} = 30V, I_D = 50A \\ R_L = 0.6\Omega, V_{GS} = 10V \\ R_{GS} = 3.6\Omega \\ (Figure 13)$		-	-	95	ns
Turn-On Delay Time	t _{d(ON)}			-	12	-	ns
Rise Time	t _r			-	55	-	ns
Turn-Off Delay Time	t _{d(OFF)}			-	37	-	ns
Fall Time	t _f			-	13	-	ns
Turn-Off Time	tOFF			-	-	75	ns
Total Gate Charge	Q _{g(TOT)}	$V_{GS} = 0$ to 20V	$V_{DD} = 48V, I_D = 50A,$	-	125	150	nC
Gate Charge at 10V	Q _{g(10)}	V _{GS} = 0 to 10V	$R_{L} = 0.96\Omega$ $I_{g(REF)} = 1.45mA$	-	67	80	nC
Threshold Gate Charge	Q _{g(TH)}	$V_{GS} = 0$ to 2V	(Figure 13)	-	3.7	4.5	nC
Input Capacitance	C _{ISS}	V _{DS} = 25V, V _{GS} = 0V f = 1MHz (Figure 12)		-	2020	-	pF
Output Capacitance	C _{OSS}			-	600	-	pF
Reverse Transfer Capacitance	C _{RSS}			-	200		pF
Thermal Resistance Junction to Case	R _{θJC}	(Figure 3)		-	-	1.14	°C/W
Thermal Resistance Junction to Ambient	R _{θJA}	TO-220		-	-	62	°C/W
		-		-	-	-	-

Source to Drain Diode Specifications

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	ТҮР	MAX	UNITS
Source to Drain Diode Voltage	V _{SD}	I _{SD} = 50A	-	-	1.5	V
Reverse Recovery Time	t _{rr}	$I_{SD} = 50A$, $dI_{SD}/dt = 100A/\mu s$	-	-	125	ns

Typical Performance Curves Unless Otherwise Specified

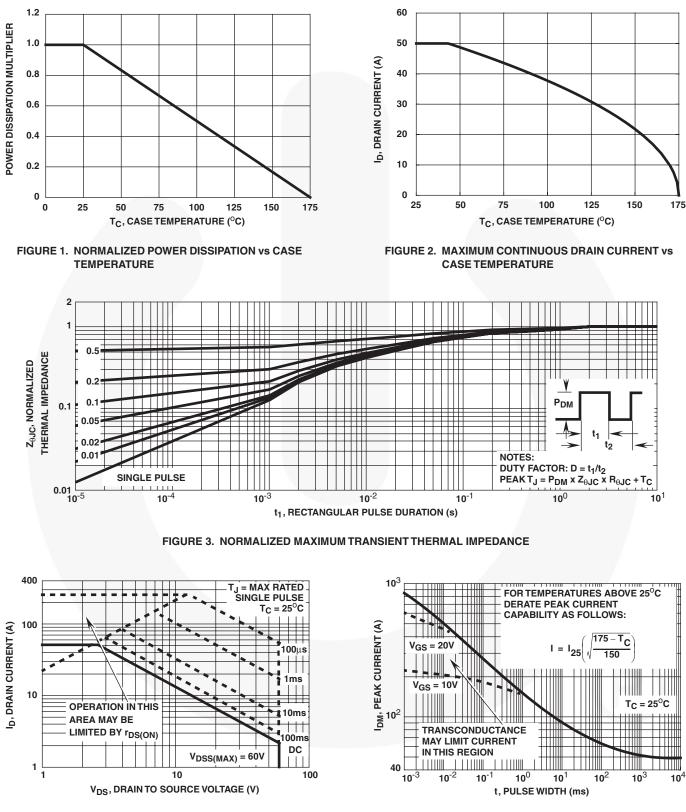
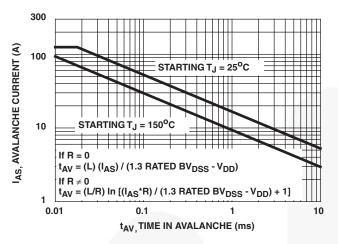


FIGURE 4. FORWARD BIAS SAFE OPERATING AREA



Typical Performance Curves Unless Otherwise Specified (Continued)





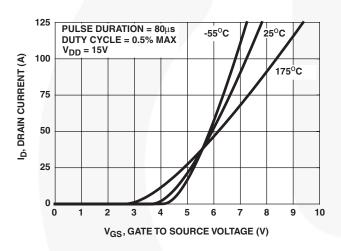


FIGURE 8. TRANSFER CHARACTERISTICS

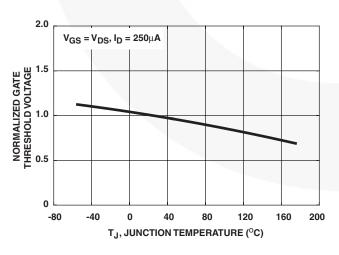
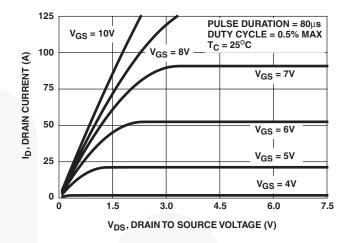


FIGURE 10. NORMALIZED GATE THRESHOLD VOLTAGE vs JUNCTION TEMPERATURE





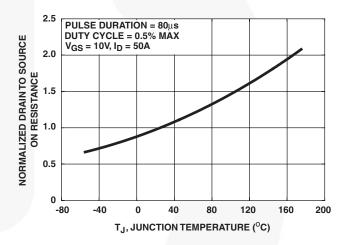


FIGURE 9. NORMALIZED DRAIN TO SOURCE ON RESISTANCE vs JUNCTION TEMPERATURE

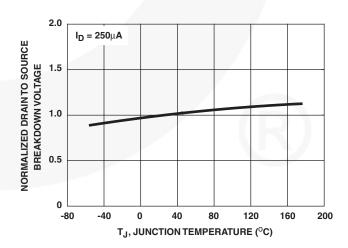


FIGURE 11. NORMALIZED DRAIN TO SOURCE BREAKDOWN VOLTAGE vs JUNCTION TEMPERATURE



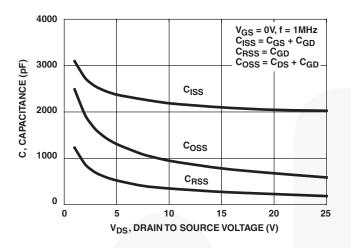
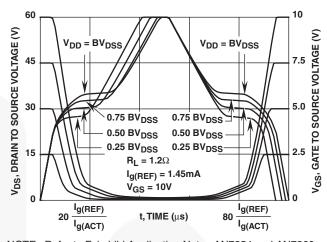


FIGURE 12. CAPACITANCE vs DRAIN TO SOURCE VOLTAGE



NOTE: Refer to Fairchild Application Notes AN7254 and AN7260. FIGURE 13. NORMALIZED SWITCHING WAVEFORMS FOR CONSTANT GATE CURRENT

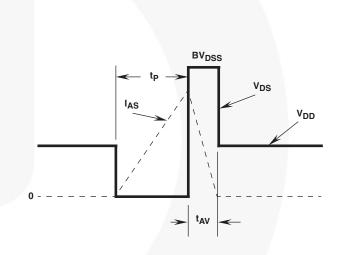


FIGURE 15. UNCLAMPED ENERGY WAVEFORMS

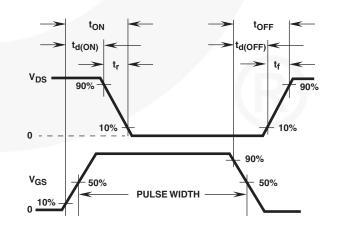


FIGURE 17. SWITCHING WAVEFORMS

Test Circuits and Waveforms

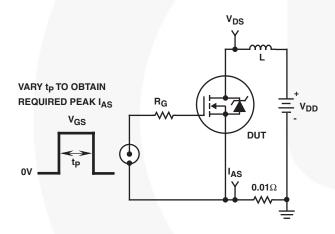


FIGURE 14. UNCLAMPED ENERGY TEST CIRCUIT

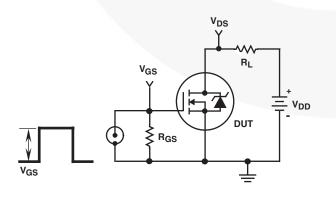


FIGURE 16. SWITCHING TIME TEST CIRCUIT

Test Circuits and Waveforms (Continued)

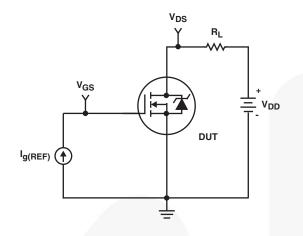
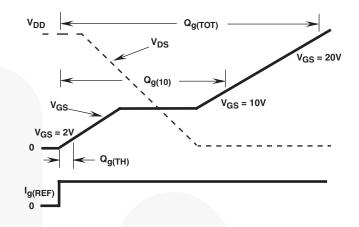


FIGURE 18. GATE CHARGE TEST CIRCUIT





PSPICE Electrical Model

SUBCKT RFP50N06 2 1 3

REV 2/22/93

*NOM TEMP = $25^{\circ}C$

CA 12 8 3.68e-9 CB 15 14 3.625e-9 CIN 6 8 1.98e-9

DBODY 7 5 DBDMOD DBREAK 5 11DBKMOD DPLCAP 10 5 DPLCAPMOD

EBREAK 11 7 17 18 64.59 EDS 14 8 5 8 1 EGS 13 8 6 8 1 ESG 6 10 6 8 1 EVTO 20 6 18 8 1

IT 8 17 1

LDRAIN 2 5 1e-9 LGATE 1 9 5.65e-9 LSOURCE 3 7 4.13e-9

MOS1 16 6 8 8 MOSMOD M=0.99 MOS2 16 21 8 8 MOSMOD M=0.01

RBREAK 17 18 RBKMOD 1 RDRAIN 5 16 RDSMOD 1e-4 RGATE 9 20 0.690 RIN 6 8 1e9 RSOURCE 8 7 RDSMOD 12e-3 RVTO 18 19 RVTOMOD 1

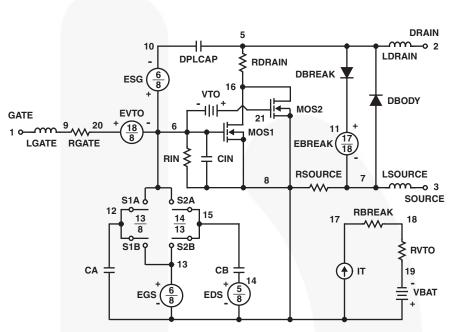
S1A 6 12 13 8 S1AMOD S1B 13 12 13 8 S1BMOD S2A 6 15 14 13 S2AMOD S2B 13 15 14 13 S2BMOD

VBAT 8 19 DC 1 VTO 21 6 0.678

.MODEL DBDMOD D (IS=9.85e-13 RS=4.91e-3 TRS1=2.07e-3 TRS2=2.51e-7 CJO=2.05e-9 TT=4.33e-8) .MODEL DBKMOD D (RS=1.98e-1 TRS1=2.35E-4 TRS2=-3.83e-6) .MODEL DPLCAPMOD D (CJO=1.42e-9 IS=1e-30 N=10) .MODEL MOSMOD NMOS (VTO=3.65 KP=35 IS=1e-30 N=10 TOX=1 L=1u W=1u) .MODEL RBKMOD RES (TC1=1.23e-3 TC2=-2.34e-7) .MODEL RDSMOD RES (TC1=5.01e-3 TC2=-1.49e-5) .MODEL RDSMOD RES (TC1=5.03e-3 TC2=-5.16e-6) .MODEL S1AMOD VSWITCH (RON=1e-5 ROFF=0.1 VON=-6.75 VOFF=-2.5) .MODEL S1BMOD VSWITCH (RON=1e-5 ROFF=0.1 VON=-2.5 VOFF=-6.75) .MODEL S2AMOD VSWITCH (RON=1e-5 ROFF=0.1 VON=-2.7 VOFF=2.3) .MODEL S2BMOD VSWITCH (RON=1e-5 ROFF=0.1 VON=-2.3 VOFF=-2.7)

.ENDS

NOTE: For further discussion of the PSPICE model consult **A New PSPICE Sub-Circuit for the Power MOSFET Featuring Global Temperature Options;** authors, William J. Hepp and C. Frank Wheatley.





SEMICONDUCTOR

TRADEMARKS

The following includes registered and unregistered trademarks and service marks, owned by Fairchild Semiconductor and/or its global subsidiaries, and is not intended to be an exhaustive list of all such trademarks.

AccuPower™	F-PFS™		Sync-Lock™
AX-CAP [®] *	FRFET [®]		SYSTEM ®*
BitSiC™	Global Power Resource SM	PowerTrench [®]	GENERAL
Build it Now™	GreenBridge™	PowerXS™	
CorePLUS™	Green FPS™	Programmable Active Droop™	TinyBoost [®]
CorePOWER™	Green FPS™ e-Series™	QFET®	TinyBuck®
CROSSVOLT™	Gmax™	QS™	TinyCalc™
CTL™	GTO™	Quiet Series™	TinyLogic [®]
Current Transfer Logic™	IntelliMAX™	RapidConfigure™	TINYOPTO™
DEUXPEED®	ISOPLANAR™	TM	TinyPower™
Dual Cool™	Marking Small Speakers Sound Loude		TinyPWM™
EcoSPARK®	and Better™	Saving our world, 1mW/W/kW at a time™	TinyWire™
EfficentMax™	MegaBuck™	SignalWise™	TranSiC™
ESBC™	MICROCOUPLER™	SmartMax™	TriFault Detect™
ESBC		SMART START™	TRUECURRENT [®] *
<u> </u>	MicroPak™	Solutions for Your Success™	µSerDes™
	MicroPak2™	SPM [®]	
Fairchild®		STEALTH™	Ser <mark>Des</mark> ™
Fairchild Semiconductor [®]	MillerDrive™		UHC®
FACT Quiet Series™	MotionMax™	SuperFET [®]	Ultra FRFET™
FACT®	mWSaver®	SuperSOT™-3	UniFET™
FAST [®]	OptoHiT™	SuperSOT™-6	VCX™
FastvCore™	OPTOLOGIC [®]	SuperSOT™-8	VisualMax™
FETBench™	OPTOPLANAR®	SupreMOS®	Visualiviax ·····

*Trademarks of System General Corporation, used under license by Fairchild Semiconductor.

DISCLAIMER

FPS™

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

SvncFET™

LIFE SUPPORT POLICY FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used here in:

- 1 Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury of the user.
- 2 A critical component in any component of a life support, device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness

VoltagePlus™

XS™

ANTI-COUNTERFEITING POLICY

Fairchild Semiconductor Corporation's Anti-Counterfeiting Policy. Fairchild's Anti-Counterfeiting Policy is also stated on our external website, www.Fairchildsemi.com, under Sales Support.

Counterfeiting of semiconductor parts is a growing problem in the industry. All manufactures of semiconductor products are experiencing counterfeiting of their parts. Customers who inadvertently purchase counterfeit parts experience many problems such as loss of brand reputation, substandard performance, failed application, and increased cost of production and manufacturing delays. Fairchild is taking strong measures to protect ourselves and our customers from the proliferation of counterfeit parts. Fairchild strongly encourages customers to purchase Fairchild parts either directly from Fairchild or from Authorized Fairchild Distributors who are listed by country on our web page cited above. Products customers buy either from Fairchild directly or from Authorized Fairchild Distributors are genuine parts, have full traceability, meet Fairchild's quality standards for handing and storage and provide access to Fairchild's full range of up-to-date technical and product information. Fairchild and our Authorized Distributors will stand behind all warranties and will appropriately address and warranty issues that may arise. Fairchild will not provide any warranty coverage or other assistance for parts bought from Unauthorized Sources. Fairchild is committed to combat this global problem and encourage our customers to do their part in stopping this practice by buying direct or from authorized distributors.

PRODUCT STATUS DEFINITIONS Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at <u>www.onsemi.com/site/pdf/Patent-Marking.pdf</u>. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor haves against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death a

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800–282–9855 Toll Free USA/Canada Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910

Japan Customer Focus Center Phone: 81-3-5817-1050 ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative

© Semiconductor Components Industries, LLC

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

onsemi: RFP50N06